

The magnetic properties of digital magnetic heterostructures δ -doped with Cr or Mn

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1. Introduction

Due to the possibility of application for spintronics, diluted magnetic semiconductors (DMSs), composed of a semiconductor and a metal, have been widely investigated [1,2]. Recently, the magnetic properties of GaAs-based digital magnetic heterostructures (DMHs), δ -doped with Cr or Mn, have been reported [1]. The obtained results were ambiguous: the half-metallicity of the compounds was revealed when the calculations were carried out with local spin density approximation, but when many-body correlations were additionally concerned, the half-metallic gaps in the electronic structure of the compounds were closed.

In order to investigate in detail the nature of possible half-metallicity in GaAs/MeAs (Me=Cr, Mn) DMHs, we studied the electronic and magnetic properties of several superstructures, in which the thickness of the GaAs spacer varied from 5 to 7 layers.

2. computational model and method

Each superstructure consisted of 8 repeated layers in [001] direction. The least doped structure was the one with 7 layers of GaAs sandwiched with a layer of MeAs, in which 50% of Ga atoms in one layer were substituted by the transition metal atom (Cr or Mn). The system richest in dopants consisted of 5 layers of GaAs sandwiched with 3 layers of MeAs (Me=Cr, Mn). For example, in Fig. 1 we show a schematic layer-by-layer atomic structure of $(\text{Ga-MnAs})_1/(\text{GaAs})_7$ supercell.

All the calculations were performed with the use of an all-electron full-potential linearized augmented plane wave (FLAPW) method within the generalized gradient approximation [3-5]. The Kohn-Sham equation was solved self-consistently. Lattice harmonics with $l \leq 8$ were employed to expand the charge density, the potential, and the wavefunctions inside muffin-tin radii of 2.20 bohr for transition metals and 2.30 bohr for post-transition metals. All core electrons were treated fully relativistically, while valence states were treated scalar relativistically.

3. Results

Among the ten investigated systems, we found an integer value of the total magnetic moment (MM) per formula unit in eight of them. The two systems for which the calculated total MMs per formula units were non-integer were those with the largest amount of doped Mn in the same composition in which Mn is substituted by Cr atom exhibit half-metallicity. The results obtained in our calculations let us analyze charge density distribution within the investigated systems and, specifically, the changes in the electronic density due to the various amount of Mn or Cr dopants. The presence of magnetic centers in the superstructures rather weakly influences the properties of the Ga atoms in the structures. The atoms do not gain a significant magnetic moment due to the interactions with Mn or Cr. As for As atoms, if the structures contain two or more transition metal atoms per

supercell, the As atom closest to the magnetic center gains negative MM that may be as large as $-0.254 \mu_B$ in the $(\text{CrAs})_2/(\text{GaAs})_6$.

In our paper, we will present a detailed discussion of the quantitative results and we will analyze the derived density of electronic states for the investigated systems.

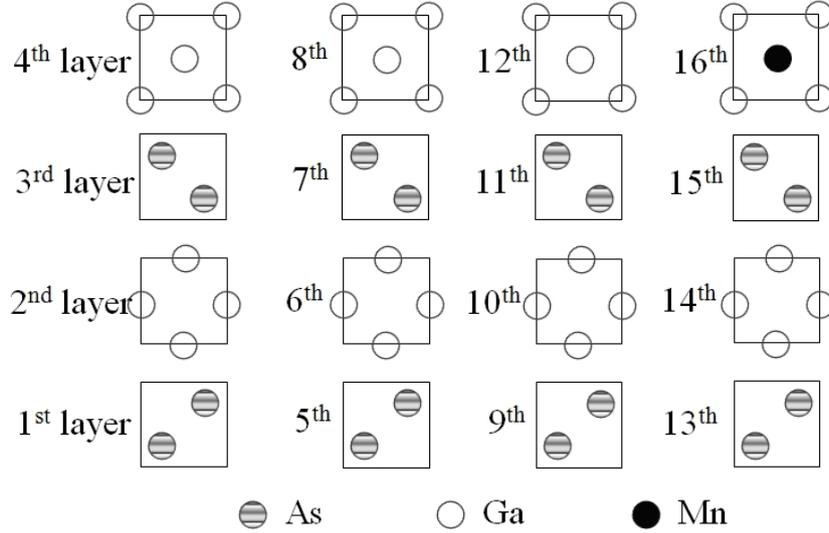


Fig. 1. A schematic view of the subsequent atomic layers in $(\text{Ga-MnAs})_1/(\text{GaAs})_7$ supercell.

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